

# PAPER TEMPLATE FOR VLSI DESIGN/CAD SYMPOSIUM 2013

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## ABSTRACT

Put your abstract here.

## 1. INTRODUCTION

Put the paper introduction here.

## 2. IMPORTANT RULES

The paper cannot exceed 2 pages, including images. Please do not paginate your paper.

The first paragraph in each section should not be indented, but all following paragraphs within the section should be indented as these paragraphs demonstrate.

Page size is A4. The top margin and bottom margin are both 25mm. The left margin and right margin are 20mm. All text must be in a two-column format and the font size should be larger than 9pt. The space between these two columns is 80mm.

Please use vector graphics instead of bitmap pictures for illustrations to achieve high paper quality.

Please embed all the used fonts inside the PDF file. The fonts for the text part should be Times.

For the reference part, please follow the rules of IEEE [1] [2].

### 2.1. Subheadings

Subheadings should appear in lower case (initial word capitalized) in boldface.

#### 2.1.1. Sub-subheadings

Sub-subheadings, as in this paragraph, are discouraged.

## 3. CONCLUSION

Put your conclusion here.

(a) Result 1

(b) Results 3

(c) Result 4

**Fig. 1.** Example of placing a figure with experimental results.

## 4. REFERENCES

- [1] M. Koyanagi, T. Fukushima, and T. Tanaka, "High-density through silicon vias for 3-D LSIs," *Proceedings of the IEEE*, vol. 97, no. 1, pp. 49–59, Jan. 2009.
- [2] M. Nicolaidis, N. Achouri, and L. Anghel, "A diversified memory built-in self-repair approach for nanotechnologies," in *Proc. IEEE VLSI Test Symposium (VTS)*, Napa Valley, Apr. 2004, pp. 313–318.